



## Department (Faculty)

Ingeniería Electrónica (ETSI de Telecomunicación)

## Module

Materials and Applications in Nanotechnology

## Code

43000340

## ECTS credits

6

## Type

Optativa

## Year/Semester

1/2

## Schedule

2nd quarter

## Language

English

## Objectives

Continuation of the module Nanotechnology, in the 3rd year of the Graduate program, the main objectives of this module are two:

- first, the students should achieve advanced knowledge on materials and structures used in nanotechnology, especially for applications in areas like electronics, heat transfer, fluidics, surface coatings, sensors, energy harvesting, information technology, medicine, etc. Both organic and inorganic materials will be considered. Some selected nanofabrication processes will be also presented.
- second, the students should practice the simulation of advanced nanodevices for several of the above applications. Selected cases in scaling MOSFETS, nanowire and nanotube TRTs will be considered. Students will develop skills for the assessment of critical parameters, representation of results, and their interpretation to extract conclusions.

## Prerequisites

None

## Previous knowledge recommended

Nanotechnology; Structure of Materials I,II; Quantum Physics; Instrumentation Engineering; Properties of Materials

## Coordination with other subjects

Modules of the Graduate of Materials Engineering Program

Modules of the Master of Materials Engineering Program, in particular: Functional Materials at Macro and Micro/Nanometer Scales, New Materials and Emerging Technologies, Materials for Electronic and Optoelectronic Devices, Polymeric Materials for Advanced Applications, Materials and Microfabrication Technologies for Electronic Devices, and Spintronics and Nanomagnetism

## Generic Competencies

- CG1, Use of english language
- CG2, Capacity for teamwork
- CG3, Spoken and written communication skills
- CG4, Use of communication and Information technologies
- CG7, Planning and organizational capacity
- CG9, Capacity of interdisciplinary work

**Specific Competencies**

CE1, Knowledge of the structure of materials and the techniques for their characterization and analysis  
 CE5, Capacity for autonomous learning  
 CE6, Capacity for designing, assessment, selection and manufacture of materials

**Contents and Schedule**

The contents of the course are shown in the following table. Student attendance is divided in theory and practical lessons (LM) and simulation work in the computer laboratory (LB).

The students will make individual reports (TI) or answer to exams and tests, according to the classes. Also, they will present specific reports for each of the simulation practices, according to some forms which include questions, tables, graphs, etc.

| Weeks       | Description  | LM   | LB   | Assignments/Tests            |
|-------------|--|------|------|------------------------------|
| <b>1-7</b>  | <b>PART 1 – Nanomaterials and applications</b>   |      |      |                              |
| 1 - 3       | Review of Nanomaterials<br>- Introduction to Nanotechnology<br>- Nanomaterials and nanostructures based in semiconductors, C-based nanostructures, organic materials<br>- Electronic properties of nanostructures: transport and confinement<br>- Nanofabrication and nanocharacterization | 11 h |      | TI-1, 1h                     |
| 4 - 7       | Devices and applications<br>- Nanotechnology for heat transfer, nanofluidics, surface coatings, energy harvesting, etc.<br>- Nanoelectronics for computation, memories, sensors and actuators.<br>- Nanotechnology in portable systems: inertial systems and displays.                     | 15 h |      | TI-2, 1 h                    |
| <b>8-14</b> | <b>PART 2 - Practical sessions of device simulation</b>  |      |      |                              |
| 8 - 10      | - Physics of Nanoscale MOSFETs: scaling down MOSFET, nanowire FET, CNT/G FET<br>- Basics of simulation. Software FETToy 2.0: device, model, environment, outputs   | 11 h |      | TI-3, 1 h                    |
| 11 - 14     | - Simulation 1: Introduction to MOSFET<br>- Simulation 2: Scaling transistors<br>- Simulation 3: Si NanoWire MOSFET<br>- Simulation 4: CNT / Graphene FET  |      | 16 h | TI-4<br>TI-5<br>TI-6<br>TI-7 |

A cooperative methodology will be used, favouring student-professor and student-student interactions by means of discussion sessions, team work, and individual sessions for doubt solving.

Office hours give students the opportunity to ask in-depth questions and to explore points of confusion or interest that cannot be fully addressed in class.

### Evaluation

The progress of the students will be monitored through the exams, laboratory sessions and individual assignments.

Exams: 50% (20+20+10)  
Simulations: 50%

### Bibliography

- B. Rogers, S. Pennathur, J. Adams, "Nanotechnology. Understanding small systems", 2<sup>nd</sup> ed. CRC Press (2011).
- R. Kelsall, I.W. Hamley and M. Geoghegan (eds.), "Nanoscale Science and Technology", Wiley (2005).
- V. Mitin et al., "Introduction to Nanoelectronics", Cambridge University Press (2008).
- R. Wasser (ed.), "Nanoelectronics and Information Technology", Wiley-VCH (2005).
- Bharat Bhushan (ed.), "Springer Handbook of Nanotechnology" 3<sup>rd</sup> ed., Springer (2010).

#### Simulations

- M. Lundstrom and J. Guo, "Nanoscale Transistors: Device Physics, Modeling and Simulation", Springer (2006).
- Mark Lundstrom, "Online Presentations", <https://nanohub.org/resources/5306>
- Software: *FETToy 2.0* at <https://nanohub.org/resources/107>

### Teaching Staff

Fernando Calle Gómez (CU) (coordinator)  
Elías Muñoz Merino (CU)

Jorge Pedrós Ayala (Dr)  
Fátima Romero Rojo (Dr)